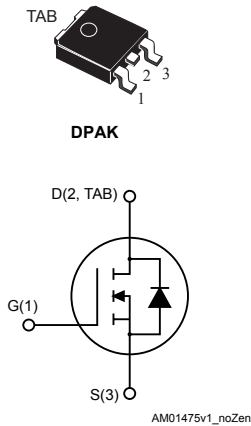


N-channel 650 V, 0.43 Ω typ., 9 A MDmesh™ II Power MOSFET in a DPAK package



Features

Order code	V_{DS} @ $T_{jmax.}$	$R_{DS(on)}$ max.	I_D
STD10NM65N	710 V	0.48 Ω	9 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Product status	
STD10NM65N	
Product summary	
Order code	STD10NM65N
Marking	10NM65N
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	9	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	5.7	A
$I_{DM}^{(1)}$	Drain current (pulsed)	36	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
dv/dt	Drain-source voltage slope ($V_{DD} = 520\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 10\text{ V}$)	25	
T_j	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Pulse width limited by safe operating area.

2. $I_{SD} \leq 9\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DSpeak} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.39	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j Max)	2.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$)	200	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$ ⁽¹⁾			100	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 4.5\text{ A}$		0.43	0.48	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	850	-	μF
C_{oss}	Output capacitance			53		
C_{rss}	Reverse transfer capacitance			4		
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0\text{ V}$	-	90	-	μF
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	25	-	nC
Q_{gs}	Gate-source charge			4		
Q_{gd}	Gate-drain charge			14		

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 4.5\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	12	-	ns
t_r	Rise time			8		
$t_{d(off)}$	Turn-off delay time			50		
$t_{f(i)}$	Fall time			20		

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		330		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	3		μC
I_{RRM}	Reverse recovery current			19		A
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		430		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	4		μC
I_{RRM}	Reverse recovery current			19		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics curves

Figure 1. Safe operating area

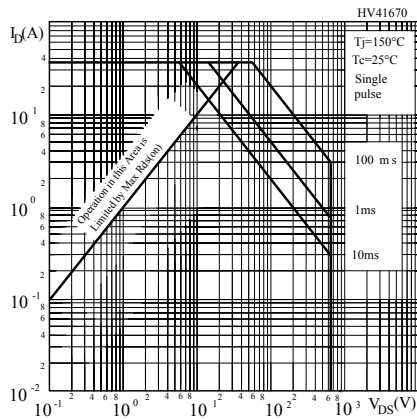


Figure 2. Thermal impedance

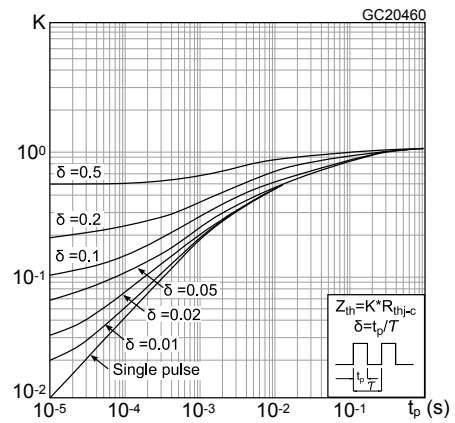


Figure 3. Output characteristics

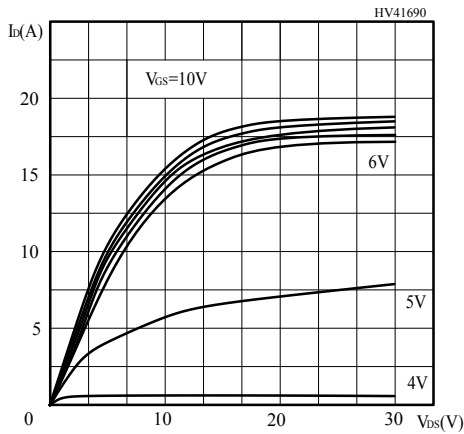


Figure 4. Transfer characteristics

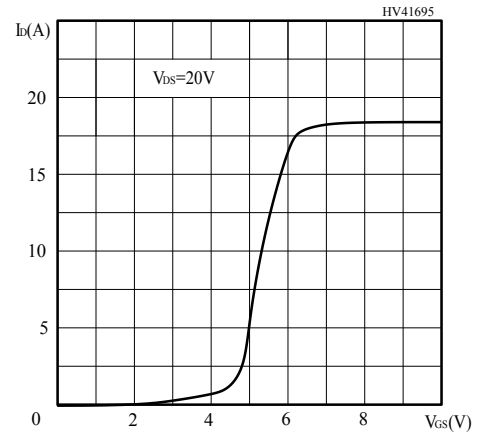


Figure 5. Static drain-source on resistance

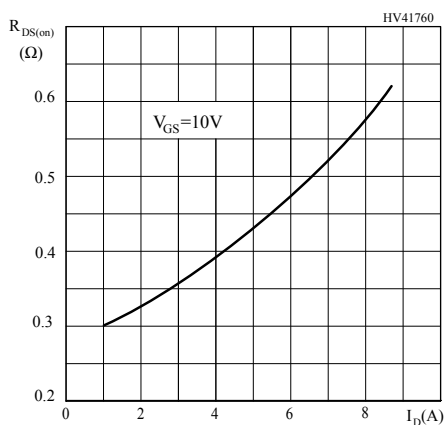


Figure 6. Gate charge vs gate-source voltage

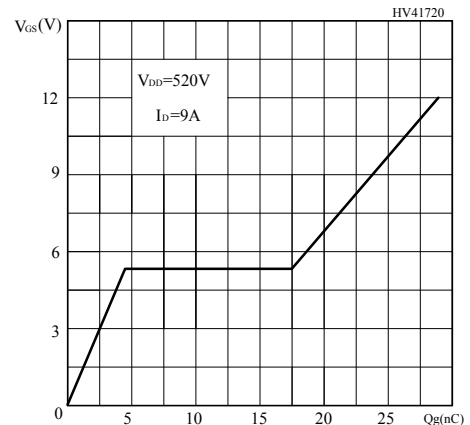


Figure 7. Capacitance variations

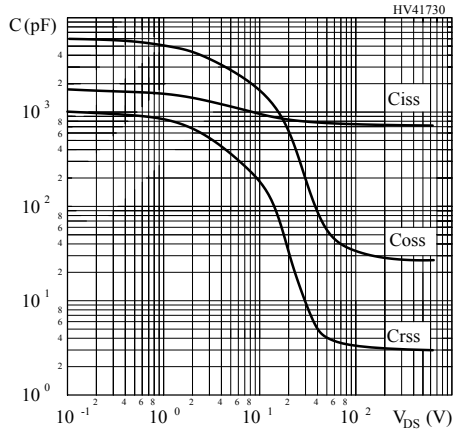


Figure 8. Normalized gate threshold voltage vs temperature

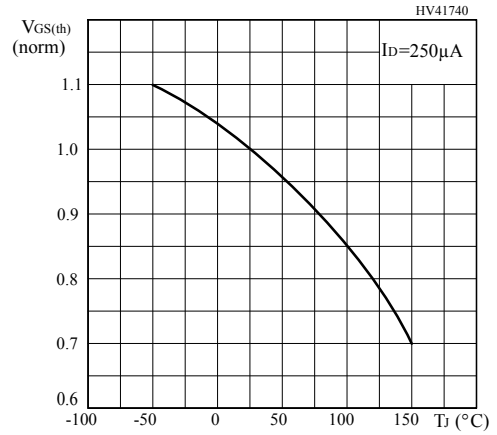


Figure 9. Normalized on resistance vs temperature

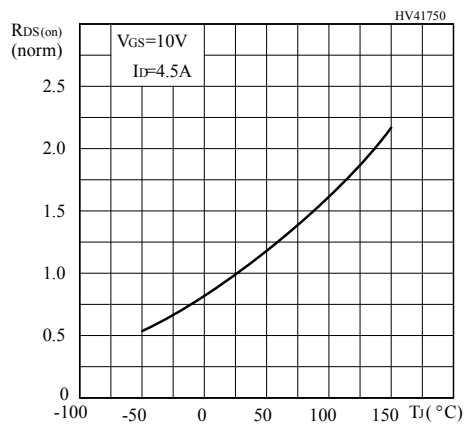


Figure 10. Source-drain diode forward characteristic

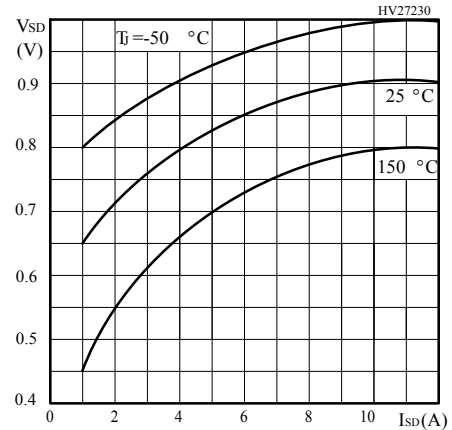
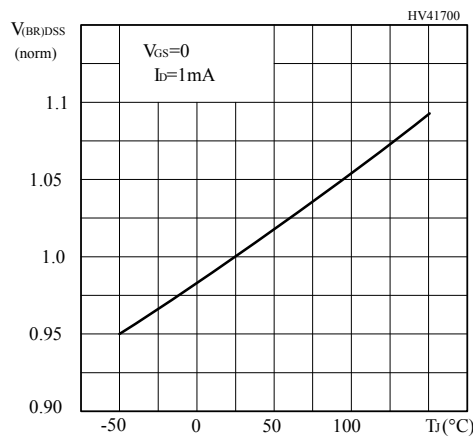
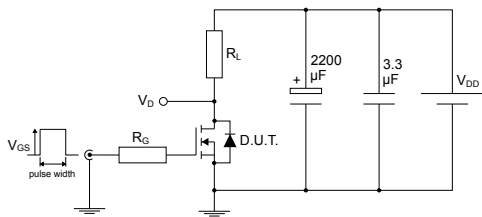


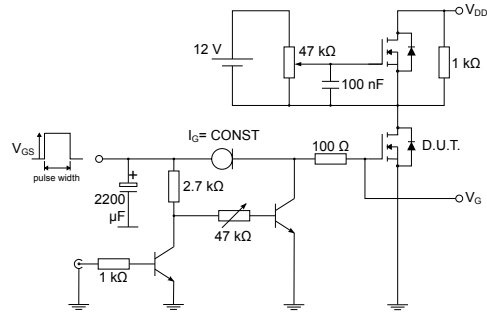
Figure 11. Normalized $V_{(BR)DSS}$ vs temperature



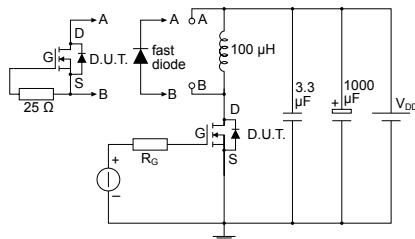
3 Test circuits

Figure 12. Test circuit for resistive load switching times


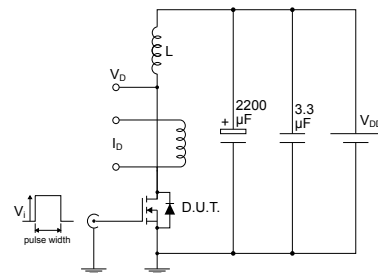
AM01468v1

Figure 13. Test circuit for gate charge behavior


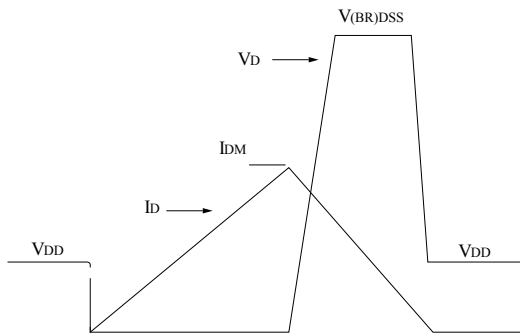
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Figure 14. Test circuit for inductive load switching and diode recovery times


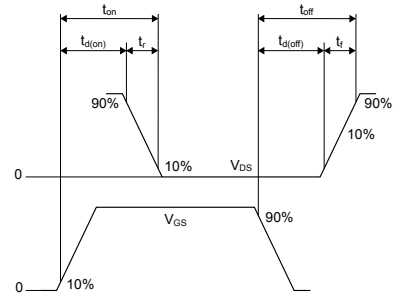
AM01470v1

Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform


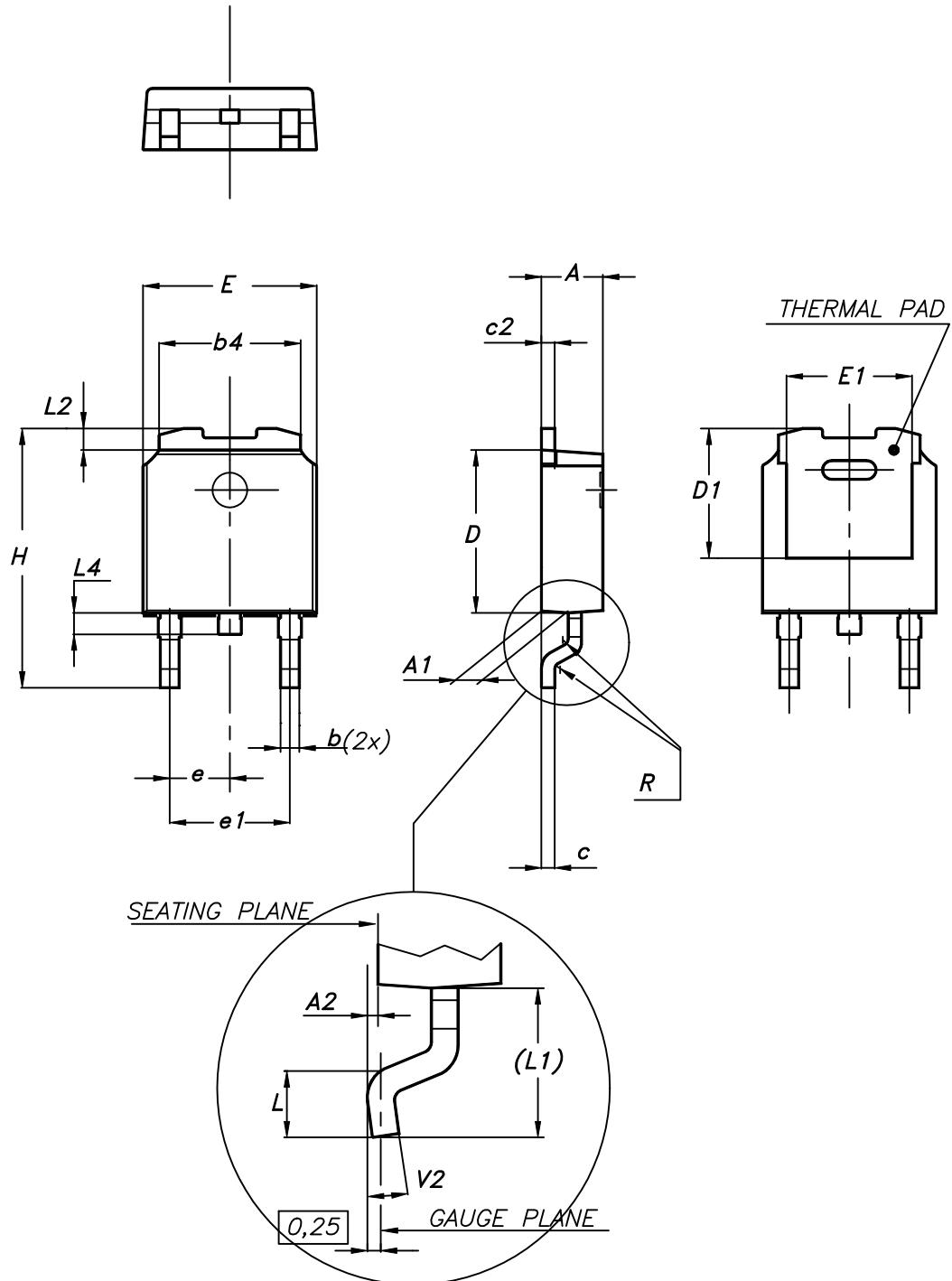
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 18. DPAK (TO-252) type A2 package outline



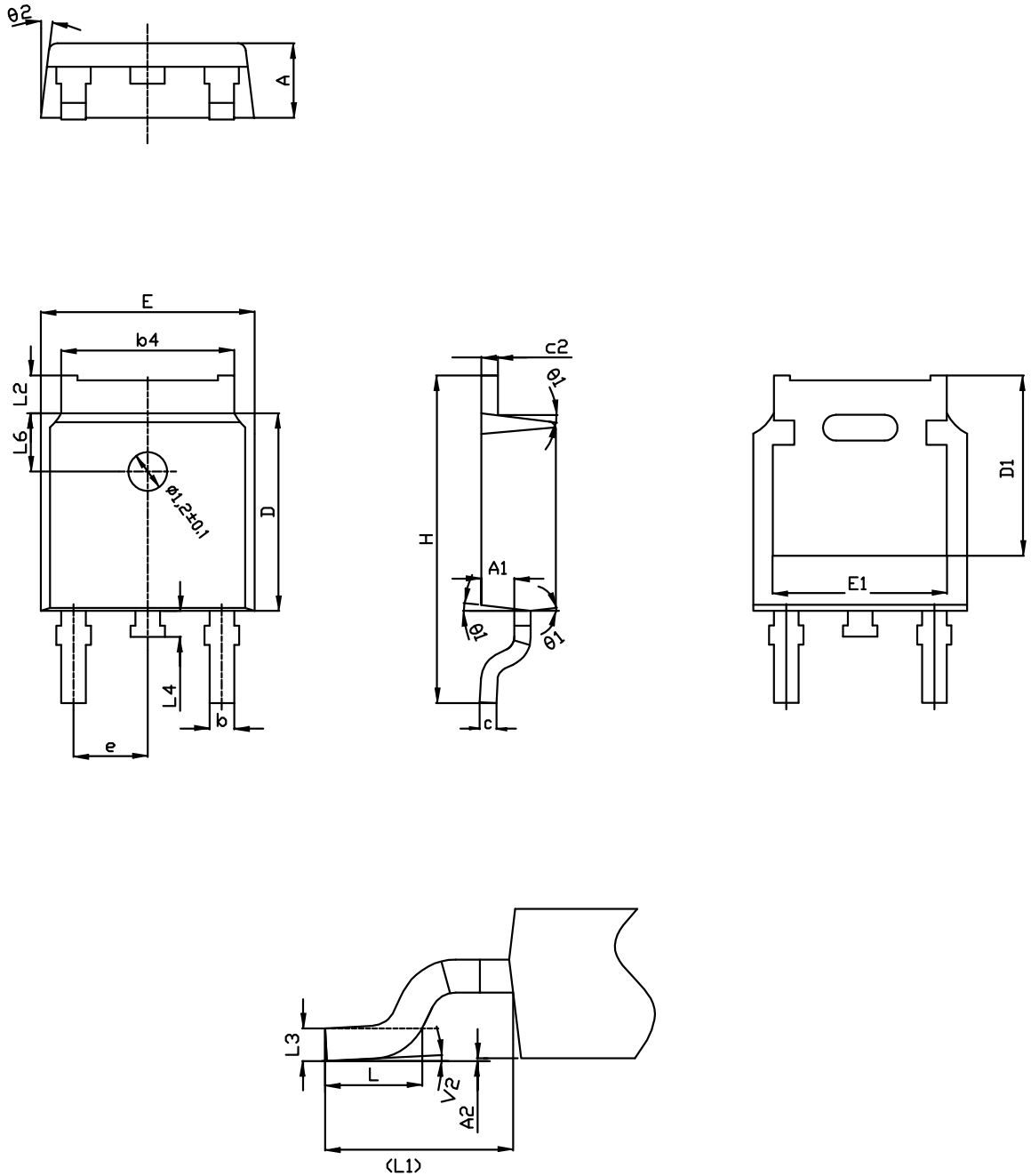
0068772_type-A2_rev25

Table 8. DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C2 package information

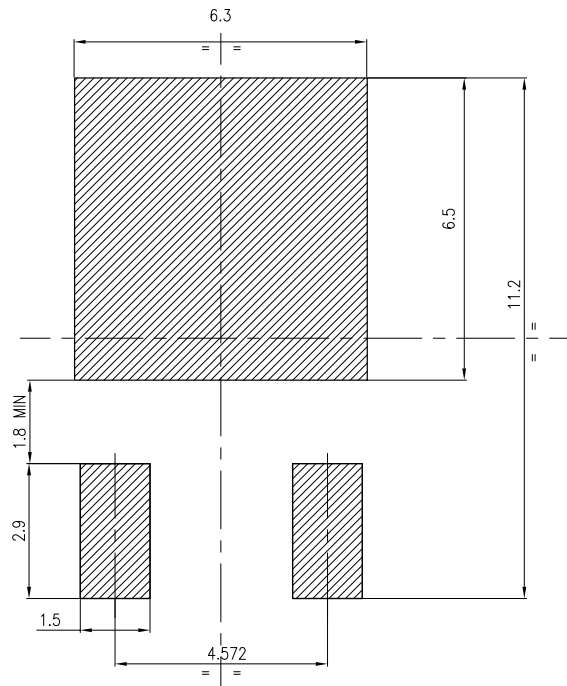
Figure 19. DPAK (TO-252) type C2 package outline



0068772_C2_25

Table 9. DPAK (TO-252) type C2 mechanical data

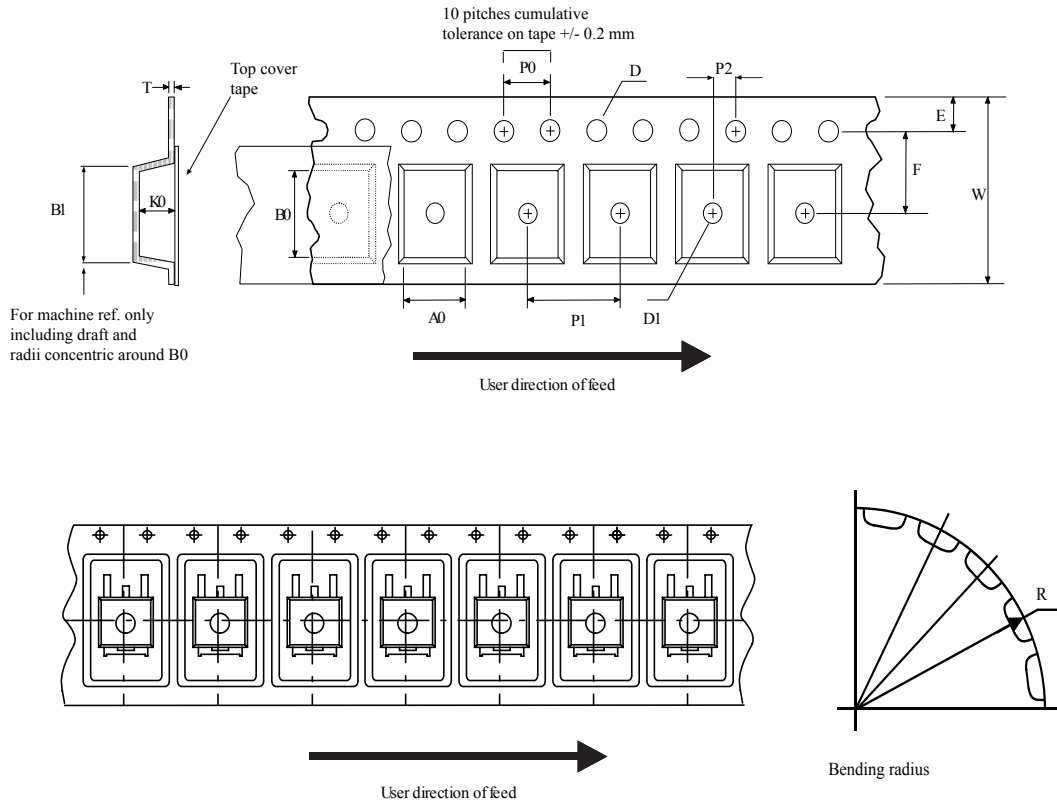
Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

Figure 20. DPAK (TO-252) recommended footprint (dimensions are in mm)


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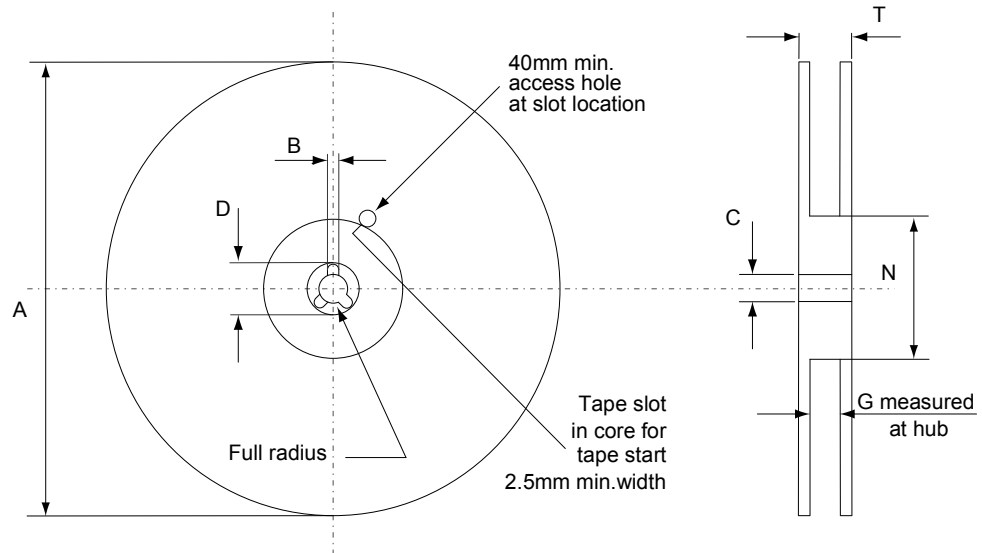
4.3 DPAK (TO-252) packing information

Figure 21. DPAK (TO-252) tape outline



AM08852v1

Figure 22. DPAK (TO-252) reel outline



AM06038v1

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 11. Document revision history

Date	Version	Changes
26-Oct-2007	1	Initial release.
07-Feb-2008	2	Document status promoted from preliminary data to datasheet.
14-Oct-2008	3	<i>Table 4: Avalanche characteristics</i> has been corrected.
16-May-2018	4	<p>The part numbers STF10NM65N, STP10NM65N and STU10NM65N have been moved to a separate datasheet.</p> <p>Removed maturity status indication from cover page. The document status is production data.</p> <p>Updated features and description in cover page, Section 1 Electrical ratings, Section 2 Electrical characteristics, Section 2.1 Electrical characteristics curves and Section 4 Package information.</p> <p>Minor text changes.</p>

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